

IN THE CLAIMS

Please amend Claims as follows:

1. (Amended) An apparatus for forming a film on a wafer in a semiconductor process comprising:

an inner part for mounting therein said wafer;

B1 an outer part covering said inner part wherein a gas inlet and a gas outlet are formed between said inner part and said outer part; and

a gas-feeding pipe partially mounted inside said gas inlet for adjusting a feeding gas flowing therein in the direction toward a vertical wall of said outer part instead of said inner part to prevent particles adhered to said inner part from peeling off, whereby said feeding gas is warmed homogeneously before reaching said inner part.

12. (Amended) A gas-feeding device for feeding a gas into a film-forming apparatus having an inner part and an outer part to form a film on a wafer mounted in said inner part, the temperature difference between said gas and said inner part being ranged from 300° C to 850° C, comprising:

B2 a gas-feeding pipe partially mounted between said inner part and said outer part for adjusting said gas flowing therein in the direction toward a vertical wall of said outer part to prevent particles adhered to said inner part from peeling off; and

a flow controller connected to said gas-feeding pipe for controlling a flow rate of said gas.

18. (Amended) A method for feeding a gas into a film-forming apparatus having an inner part and an outer part to form a film on a wafer mounted in said inner part in a semiconductor process, comprising steps of:

B3 (a) feeding said gas into a space between said outer part and said inner part and directing a flow of said gas in the direction toward a vertical wall of said outer part to prevent particles adhered to said inner part from peeling off; and

(b) leading said gas into said inner part along a path between said outer part and said inner part so that gas warms before reaching said inner part.